



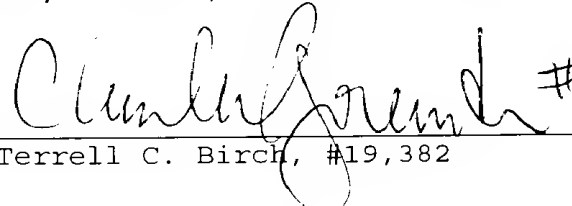
Appl. No. 09/670,820

- ☒ Petition for two (2) month(s) extension of time pursuant to 37 C.F.R. §§ 1.17 and 1.136(a). \$410.00 for the extension of time.
- ☐ No fee is required.
- ☒ Check(s) in the amount of \$410.00 is(are) enclosed.
- ☐ Please charge Deposit Account No. 02-2448 in the amount of \$0.00. This form is submitted in triplicate.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

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Attachment(s)

(Rev. 10/15/02)



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PATENT  
0717-0446P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Atsushi SHIMONAKA Conf.#: 8768  
Appl. No.: 09/670,820 Group: 2815  
Filed: September 28, 2000 Examiner: LANDAU  
For: SEMICONDUCTOR LASER ELEMENT AND  
ELECTRONIC DEVICE USING THE SAME

AMENDMENT

Assistant Commissioner for Patents  
Washington, DC 20231

January 27, 2003

Sir:

In response to the Office Action dated August 28, 2002, the period for response being extended to January 28, 2003, please amend the above identified patent application as follows.

IN THE SPECIFICATION

Please replace the paragraph beginning on page 34, line 16 and ending on page 35, line 7, with the following rewritten paragraph:

Figure **6** is a perspective view showing a semiconductor laser device **20** according to embodiment 3 of the present invention. The semiconductor laser device **20** includes a semiconductor substrate **21** made of n-type GaAs. The semiconductor substrate **21** has a rectangular surface in which the longitudinal length is 1096  $\mu\text{m}$ , and the width is 30 $\mu\text{m}$ . (Hereinafter, the longitudinal direction of the semiconductor substrate **21** and the direction of

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